

ABSTRACT

A method of manufacturing a field effect transistor of the present invention includes: applying a coating liquid 20 containing a solvent 13 as
5 well as first and second organic molecules 11 and 12 that have been dissolved in the solvent 13; and forming a first layer and a second layer by removing the solvent 13 contained in the coating liquid 20 that has been applied. The first layer contains the first organic molecules 11 as its main component. The second layer adjoins the first layer and contains the second organic
10 molecules 12 as its main component. The first organic molecules 11 are a semiconductor material or a precursor of a semiconductor material. The second organic molecules 12 are an insulator material or a precursor of an insulator material. The first organic molecules 11 and the second organic molecules 12 are not compatible with each other.